Thyristor Semiconductor Device - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-00-415-8419

Inclosure Material:
Metal
Overall Length:
Between 0.330 inches and 0.505 inches
Overall Diameter:
0.650 inches
Mounting Facility Quantity:
1
Internal Configuration:
Junction contact
Mounting Method:
Threaded stud
Features Provided:
Hermetically sealed case
Overall Width Across Flats:
Between 0.544 inches and 0.562 inches
Thread Size:
0.250 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
100.0 breakover voltage, dc
Current Rating Per Characteristic:
7.50 amperes source cutoff current
Power Rating Per Characteristic:
2.0 watts small-signal input power, common-collector blank
Maximum Operating Tempurature Per Measurement Point:
120.0 degrees celsius ambient air
Special Features:
Junction pattern arrangement: pnp
Thread Series Designator:
Unf
Terminal Type And Quantity:
1 threaded stud and 2 tab, solder lug
Specification Data:
80131-release5040 professional/industrial association specification
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No

NSN 5961-00-415-8419

Thyristor Semiconductor Device - Page 2 of 2

Fiig: A110a0

